	Application No.	**Applicant(s)**	
Notice of Allowability	10/721,979	SHIEH ET AL.	
	Examiner	**Art Unit**	
	David Nhu	2818	

-- The MAILING DATE of this communication appears on the cover sheet with the correspondence address--

All claims being allowable, PROSECUTION ON THE MERITS IS (OR REMAINS) CLOSED in this application. If not included herewith (or previously mailed), a Notice of Allowance (PTOL-85) or other appropriate communication will be mailed in due course. **THIS NOTICE OF ALLOWABILITY IS NOT A GRANT OF PATENT RIGHTS.** This application is subject to withdrawal from issue at the initiative of the Office or upon petition by the applicant. See 37 CFR 1.313 and MPEP 1308.

1. ☒ This communication is responsive to *11/25/03*.

2. ☒ The allowed claim(s) is/are *1-23*.

3. ☒ The drawings filed on *25 November 2003* are accepted by the Examiner.

4. ☐ Acknowledgment is made of a claim for foreign priority under 35 U.S.C. § 119(a)-(d) or (f).

    a) ☐ All   b) ☐ Some*   c) ☐ None   of the:

      1. ☐ Certified copies of the priority documents have been received.

      2. ☐ Certified copies of the priority documents have been received in Application No. _____ .

      3. ☐ Copies of the certified copies of the priority documents have been received in this national stage application from the International Bureau (PCT Rule 17.2(a)).

    * Certified copies not received: _____ .

Applicant has THREE MONTHS FROM THE "MAILING DATE" of this communication to file a reply complying with the requirements noted below. Failure to timely comply will result in ABANDONMENT of this application.
THIS THREE-MONTH PERIOD IS NOT EXTENDABLE.

5. ☐ A SUBSTITUTE OATH OR DECLARATION must be submitted. Note the attached EXAMINER'S AMENDMENT or NOTICE OF INFORMAL PATENT APPLICATION (PTO-152) which gives reason(s) why the oath or declaration is deficient.

6. ☐ CORRECTED DRAWINGS (as "replacement sheets") must be submitted.

    (a) ☐ including changes required by the Notice of Draftsperson's Patent Drawing Review (PTO-948) attached

        1) ☐ hereto or 2) ☐ to Paper No./Mail Date _____ .

    (b) ☐ including changes required by the attached Examiner's Amendment / Comment or in the Office action of

    Paper No./Mail Date _____ .

    Identifying indicia such as the application number (see 37 CFR 1.84(c)) should be written on the drawings in the front (not the back) of each sheet. Replacement sheet(s) should be labeled as such in the header according to 37 CFR 1.121(d).

7. ☐ DEPOSIT OF and/or INFORMATION about the deposit of BIOLOGICAL MATERIAL must be submitted. Note the attached Examiner's comment regarding REQUIREMENT FOR THE DEPOSIT OF BIOLOGICAL MATERIAL.

Attachment(s)

1. ☒ Notice of References Cited (PTO-892)

2. ☐ Notice of Draftperson's Patent Drawing Review (PTO-948)

3. ☒ Information Disclosure Statements (PTO-1449 or PTO/SB/08), Paper No./Mail Date 01

4. ☐ Examiner's Comment Regarding Requirement for Deposit of Biological Material

5. ☐ Notice of Informal Patent Application (PTO-152)

6. ☐ Interview Summary (PTO-413), Paper No./Mail Date _____ .

7. ☐ Examiner's Amendment/Comment

8. ☒ Examiner's Statement of Reasons for Allowance

9. ☐ Other _____ .

REASONS FOR ALLOWANCE

1.   Claims 1-23 are allowed.

2.   The following is an examiner's statement of reasons for allowance: None of the references of record teaches or suggests in claims 1, 5, 14: forming a protective layer on a first region of the substrate, the first region encompassing a portion of at least one STI; forming one or more semiconductor structures in a second region, the second region not being covered by the protective layer; removing the protective layer; wherein the portion of the STI located in the second region is partially removed with respect to the STI located in the first region (as cited in claim 1); forming a protective layer on the first poly layer in a first region of the substrate; fabricating in a second region one or more semiconductor structures, the semiconductor structures utilizing at least one of the first poly layer and the oxide layer in a second region, the second region not being covered by the protective layer; forming on the substrate a second poly layer; removing the first poly layer, the protective layer, and the second poly layer from the first region (as cited in claim 5); forming a protective layer on the first poly layer and the STI filler in a first region of the substrate; implanting exposed portions of the first poly layer; fabricating in a second region one or more semiconductor structures such that the STI filler located in the second region is partially removed; removing the protective oxide layer, and the first poly layer (as cited in claim 14).

3.   Any comments considered necessary by applicant must be submitted no later than the payment of the issue fee and, to avoid processing delays, should preferably accompany the issue fee. Such submissions should be clearly labeled "Comments on Statement of Reasons for Allowance."

CONCLUSION

4. The prior art made of record and not relied upon is considered pertinent to applicant's disclosure: Yu et al (6,110,780): Using NO or N2O Treatment to Generate Different Oxide Thickness in one Oxidation Step for Single Poly Non-Volatile Memory.

5. Any inquiry concerning this communication on earlier communications from the examiner should be directed to David Nhu , (571)272-1792. The examiner can normally be reached on Monday-Friday from 7:30 AM to 5:00 PM.

The examiner's supervisor, David Nelms can be reached on (571)272-1787.

The fax phone number for the organization where this application or proceeding is assigned is (703) 872-9306.

Any inquiry of a general nature or relating to the status of this application or proceeding should be directed to the receptionist whose telephone number is (703) 308-0956

David Nhu

November 13, 2004

DAVID NHU
PRIMARY EXAMINER